

Silicon Photodiode Module

1. Features:

- High responsivity, High speed;
- Low dark current, Low capacitance;
- Planar incident structure;
- Coaxial package, Laser welding;
- Detect range 400nm-1000nm;
- RoHS compliant and lead-free.

2. Applications:

- Optical power meter;
- Optical sensor;
- Space light detect equipment.

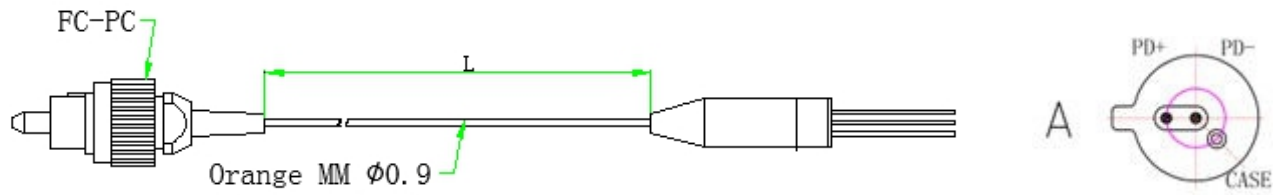
3. Absolute Maximum Ratings(Tc=25℃):

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
PD Forward current	I _{FPD}	CW	-	-	5	mA
Reverse current	I _R	CW	-	-	1000	uA
Reverse voltage	V _{RPD}	CW	-	30	-	V
Operating temperature	Top	-	-40	-	85	℃
Storage temperature	Ts	-	-40	-	+85	℃
Storage Relative Humidity	RH	-	5	-	95	%
Lead Soldering (Temp.)/(Time)	-	-		260/10		℃/Sec

4. Optical-Electro Characteristics(Tc=25℃):

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Wavelength range	λ		400	-	1000	nm
Responsivity	R	λ = 650nm	-	0.30	-	A/W
		λ = 800nm	-	0.35	-	
		λ = 900nm	-	0.40	-	
Active area	S	-	680*680			um
Dark current	I _D	V _r =0V	-	-	1.0	nA
Capacitance	C	V _r =0V	-	-	5.0	pF
Rise time/Fall time	T _R /T _F	V _r =0V, 10~90%	-	-	3.0	ns
Bandwidth	BW	3dB Bandwidth	-	100	-	MHz
Saturation power	P _s	-	2	-	-	mW
Fiber type	-	-		50/125		um

5. Package Drawing&PIN-OUT Definition(Unit:mm):



6. Order Information

BSPD-680P10-AFAM